

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Application of)
Shunpei YAMAZAKI et al.)
Based On Application No. 09/838,216) Art Unit: 2824
Which Was Filed: April 20, 2001) Examiner: M. Lebentritt
For: METHOD FOR FABRICATING)
SEMICONDUCTOR THIN FILM) Date: October 6, 2003

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, copies of some of the documents cited are enclosed.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/838,216 filed April 20, 2001, and its predecessor application Serial Nos. 09/115,838 and 08/536,977, from which priority is claimed under 35 U.S.C. 120.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By: _____


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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> | | | | Complete if Known | | | |
| | | | | Application Number | | New Application | |
| | | | | Filing Date | | October 6, 2003 | |
| | | | | First Named Inventor | | Shunpei YAMAZAKI et al. | |
| | | | | Art Unit | | 2824 | |
| | | | | Examiner Name | | M. Lebentritt | |
| Sheet | 1 | of | 2 | Attorney Docket Number | | 740756-2659 | |

| U.S. PATENT DOCUMENTS | | | | | |
|-----------------------|-----------------------|--|--------------------------------|--|---|
| Examiner Initials* | Cite No. ¹ | U.S. Patent Document | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Number - Kind Code ² (if known) | | | |
| | | US-5,700,333 | 12/23/1997 | Yamazaki et al. | |
| | | US-4,561,171 | 12/31/1985 | Schlosser | |
| | | US-5,147,826 | 09/15/1992 | Liu et al. | |
| | | US-5,229,306 | 07/20/1993 | Lindberg | |
| | | US-5,244,819 | 09/14/1993 | Yue | |
| | | US-5,275,851 | 01/04/1994 | Fonash et al. | |
| | | US-5,441,899 | 08/15/1995 | Nakai | |
| | | US-5,444,001 | 08/22/1995 | Tokuyama | |
| | | US-5,529,937 | 06/25/1996 | Zhang | |
| | | US-5,696,011 | 12/09/1997 | Nakata et al. | |
| | | US-5,796,116 | 08/18/1998 | Nakata et al., | |
| | | US-5,828,429 | 10/27/1998 | Takemura | |
| | | US-5,899,709 | 05/04/1999 | Yamzaki et al. | |
| | | US-6,048,758 | 04/11/2000 | Yamazaki et al. | |

| FOREIGN PATENT DOCUMENTS | | | | | | |
|--------------------------|-----------------------|---|--------------------------------|--|---|--------------------|
| Examiner Initials* | Cite No. ¹ | Foreign Patent Document | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
| | | Country Code ³ Number ⁴ Kind Code ⁵ (if known) | | | | |
| | | JP6333824 | 12/02/1994 | | | Abstract |
| | | JP6333825 | 12/02/1994 | | | Full & Abstract |
| | | JP 03-229415 | 10/11/1991 | | | Abstract |
| | | JP 06-333824 | 12/02/1994 | | | Abstract |

| OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS | | | |
|---|-----------------------|---|----------------|
| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
| | | DVURECHENSKI.A, TRANSPORT PHENOMENA IN AMORPHOUS SILICON DOPED BY ION IMPLANTATION OF 3D METALS, PP.635-640PHYS. STAT. SOL. | |
| | | HAYZELDEN.C, IN SITU TRANSMISSION ELECTRON MICROSCOPY STUDIES OF SILICIDE-MEDIATED CRYSTALLIZATION OF AMORPHOUS SILICON, VOL.60/PP.225-227APPL. PHYS. LETT. | |
| | | HEMPEL.T, NEEDLE-LIKE CRYSTALLIZATION OF NI DOPED AMORPHOUS SILICON THIN FILMS, VOL.85/PP.921-92450LID STATE COMMUNICATIONS | |
| | | KAKKAD.R, CRYSTALLIZED SI FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING OF AMORPHOUS SILICON, VOL. 65/PP. 2069-2072J. APPL. PHYS. | |
| | | KAKKAD.R, LOW TEMPERATURE SELECTIVE CRYSTALLIZATION OF AMORPHOUS SILICON, VOL. 1151PP.66-68JOURNAL OF NON-CRYSTALLINE SOLIDS | |

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| Examiner Signature | | Date Considered | |
|--------------------|--|-----------------|--|

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| | | | | Art Unit | | 2854 | |
| | | | | Examiner Name | | M. Lebentritt | |
| Sheet | 2 | of | 2 | Attorney Docket Number | | 740756-2659 | |

| U.S. PATENT DOCUMENTS | | | | | |
|--------------------------------|-----------------------|--|--------------------------------|--|---|
| Examiner Initials [*] | Cite No. ¹ | U.S. Patent Document | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| | | Number - Kind Code ² (if known) | | | |
| | | US-5,789,284 | 08/1998 | Yamazaki et al. | |
| | | US-6,331,457 | 12/2001 | Yamazaki et al. | |
| | | US-6,218,219 | 04/2001 | Yamazaki et al. | |
| | | US-6,197,624 | 03/2001 | Yamazaki | |
| | | US-6,048,758 | 04/2000 | Yamazaki et al. | |
| | | US-6,348,368 | 02/2002 | Yamazaki et al. | |
| | | US-2001/0041397 | 05/2001 | Fukushima | |
| | | US-2002/0013114 | 07/2001 | Ohtani et al. | |
| | | US-6,013,544 | 01/11/2000 | Makita et al. | |
| | | | | | |

| FOREIGN PATENT DOCUMENTS | | | | | | |
|--------------------------------|-----------------------|--|--------------------------------|--|---|----------------|
| Examiner Initials [*] | Cite No. ¹ | Foreign Patent Document | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
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| | | LIU.G, SELECTIVE AREA CRYSTALLIZATION OF AMORPHOUS SILICON FILMS BY LOW-TEMPERATURE RAPID THERMAL ANNEALING, VOL. 551PP.660-662APPL. PHYS. LETT. | |
| | | LIU.G, "POLYCRYSTALLINE SILICON THIN FILM TRANSISTORS ON CORNING 7059 GLASS SUBSTRATES USING SHORT TIME, VOL. 62/PP.2554-2556APPL. PHYS. LETT. | |
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